



DMP4025SFGQ

**40V P-CHANNEL ENHANCEMENT MODE MOSFET** PowerDI3333-8

## **Product Summary**

BV <sub>DSS</sub>	R <sub>DS(ON)</sub> Max	I <sub>D</sub> Max T <sub>A</sub> = +25°C (Note 7)
-40V	$25m\Omega @ V_{GS} = -10V$	- 7.2A
	$45mΩ @ V_{GS} = -4.5V$	- 5.4A

## Description

This MOSFET has been designed to minimize the on-state resistance and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

# Applications

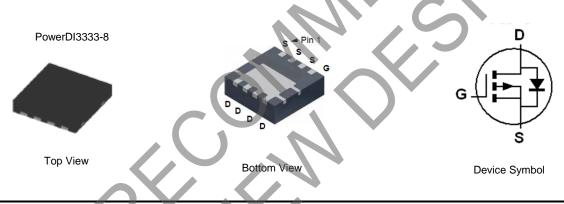
- Motor Control
- Backlighting
- **DC-DC Converters**
- Printer Equipment

## Features

- Low R<sub>DS(ON)</sub> Minimizes Conduction Losses
- Fast Switching Speed Minimizes Switching Losses
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

## **Mechanical Data**

- Case: PowerDI<sup>®</sup>3333-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals Connections: See Diagram Below
- Terminals: Finish Matte Tin Annealed over Copper Lead Frame. Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.0172 grams (Approximate)



## Ordering Information (Note 5)

Part Number	Marking	Reel Size (inches)	Tape Width (mm)	Quantity per Reel
DMP4025SFGQ-7	P40	7	8	2,000
DMP4025SFGQ-13	P40	13	8	3,000
Notes: 1. No purposely added lead, Fully FU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.				

1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and lead-free

Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and 1000ppm antimony compounds.

Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to https://www.diodes.com/quality/.

5. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

# Marking Information



P40 = Product Marking Code YYWW = Date Code Marking YY = Year (ex: 18 = 2018) WW = Week (01 to 53)

PowerDI is a registered trademark of Diodes Incorporated.



## **Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Drain-Source Voltage		V <sub>DSS</sub>	-40	V
Gate-Source Voltage		V <sub>GSS</sub>	±20	v
Continuous Drain Current, V <sub>GS</sub> = -10V	(Note 7)		-7.2	
	$T_A = +70^{\circ}C$ (Note 7)	ID	-5.77	
	(Note 6)		-4.65	•
Maximum Body Diode Forward Current	(Note 7)	Is	-7.2	A
Pulsed Drain Current	(Note 8)	I <sub>DM</sub>	-80	
Pulsed Source Current	(Note 8)	I <sub>SM</sub>	-80	

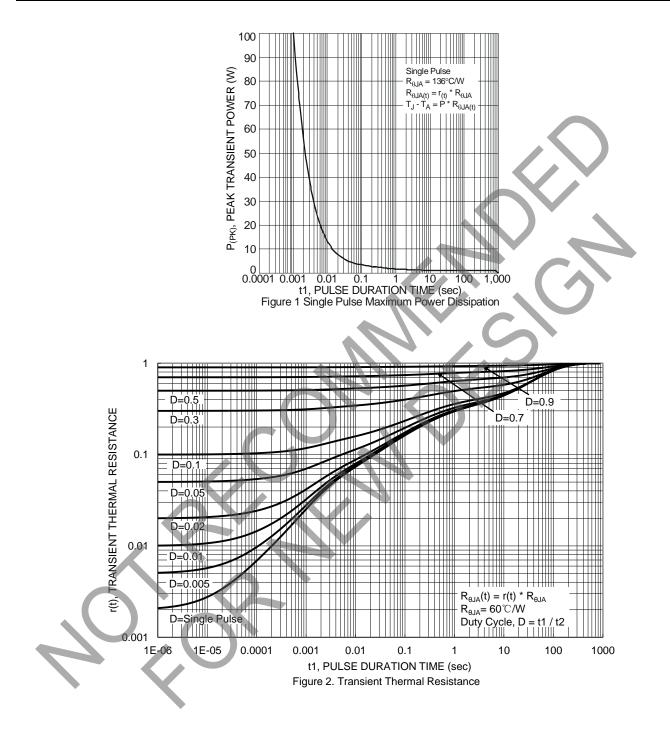
## **Thermal Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

-				
Characteristic		Symbol	Value	Unit
Power Dissipation	(Note 6)		0.81	14/
Linear Derating Factor	(Note 7)	PD PD	1.95	W
Thermal Resistance, Junction to Ambient	(Note 6)		155	°C/W
mermai Resistance, Junction to Ambient	(Note 7)	Reja	64	C/VV
Operating and Storage Temperature Range		TJ, T <sub>STG</sub>	-55 to +150	°C

Notes:
6. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
7. For a device surface mounted on 25mm x 25mm FR-4 PCB with 2oz copper, in still air conditions.
8. Same as note (7), except the device is pulsed with D= 0.02 and pulse width 300µs.



### **Thermal Characteristics**





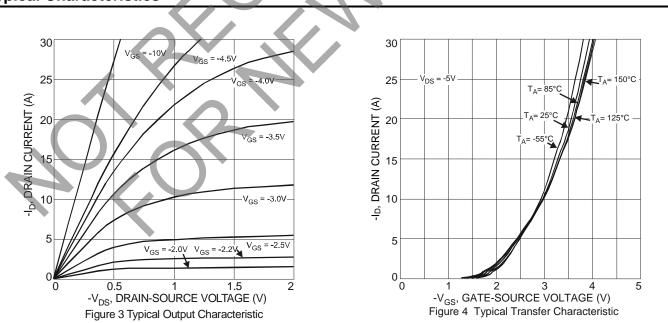
# Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

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Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS			1		1		
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	-40		_	V	$I_{D} = -250 \mu A, V_{GS} = 0 V$	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>		—	-1.0	μA	$V_{DS} = -40V, V_{GS} = 0V$	
Gate-Source Leakage	I <sub>GSS</sub>			±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS							
Gate Threshold Voltage	V <sub>GS(TH)</sub>	-0.8	-1.3	-1.8	V	$I_D = -250 \mu A$ , $V_{DS} = V_{GS}$	
Static Drain-Source On-Resistance (Note 9)	Baaraan		18	25	mΩ	$V_{GS} = -10V, I_D = -3A$	
Static Drain-Source On-Resistance (Note 9)	R <sub>DS(ON)</sub>	_	30	45	11122	$V_{GS} = -4.5V, I_D = -3A$	
Forward Transconductance (Notes 9 & 10)	<b>g</b> <sub>fs</sub>	_	16.6		S	$V_{DS} = -5V, I_{D} = -3A$	
Diode Forward Voltage (Note 9)	V <sub>SD</sub>	_	-0.7	-1.0	V	$I_{S} = -1A, V_{GS} = 0V$	
DYNAMIC CHARACTERISTICS (Note 10)							
Input Capacitance	C <sub>iss</sub>	_	1643				
Output Capacitance	Coss	_	179	_	pF	$V_{DS} = -20V, V_{GS} = 0V$ f = 1MHz	
Reverse Transfer Capacitance	C <sub>rss</sub>	_	128	+			
Gate Resistance	R <sub>g</sub>	_	6.43	1	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1MHz$	
Total Gate Charge (Note 11)	Qg	_	14.0			$V_{GS} = -4.5V$	
Total Gate Charge (Note 11)	Qg	_	33.7		nC	V <sub>DS</sub> = -20V	
Gate-Source Charge (Note 11)	Q <sub>gs</sub>	—	5.5			$V_{GS} = -10V$ $I_D = -3A$	
Gate-Drain Charge (Note 11)	Q <sub>gd</sub>	—	7.3			Ť.	
Turn-On Delay Time (Note 11)	t <sub>D(ON)</sub>	_	6.9	_			
Turn-On Rise Time (Note 11)	t <sub>R</sub>		14.7	—	ne	V <sub>DD</sub> = -20V, V <sub>GS</sub> = -10V	
Turn-Off Delay Time (Note 11)	t <sub>D(OFF)</sub>	<u> </u>	53.7	_	ns	I <sub>D</sub> = -3A	
Turn-Off Fall Time (Note 11)	t <sub>F</sub>		30.9	—			

Notes:

9. Measured under pulsed conditions. Pulse width ≤ 300µs; duty cycle ≤ 2%.
10. For design aid only, not subject to production testing.
11. Switching characteristics are independent of operating junction temperatures.

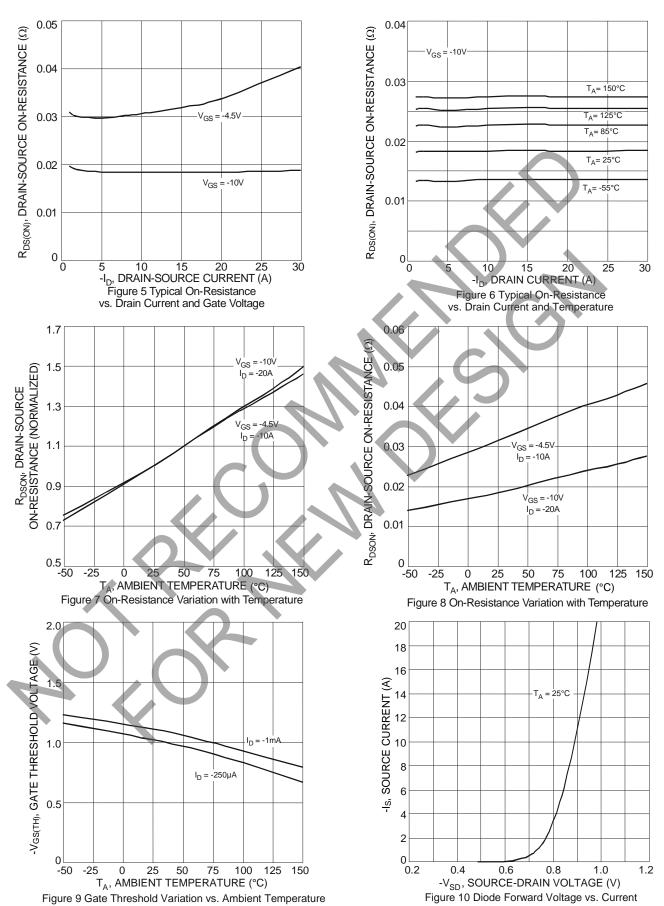
# **Typical Characteristics**





## NOT RECOMMENDED FOR NEW DESIGN USE <u>DMPH4029LFGQ</u>

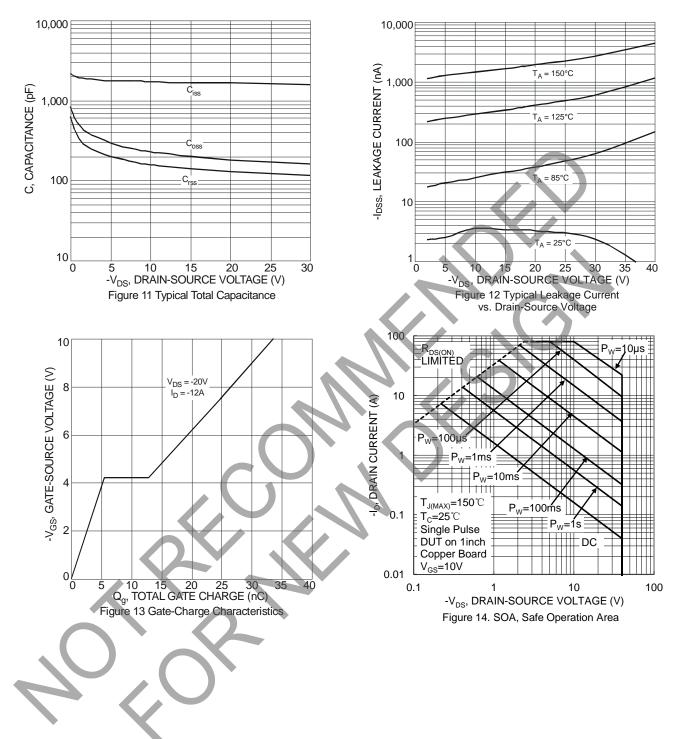
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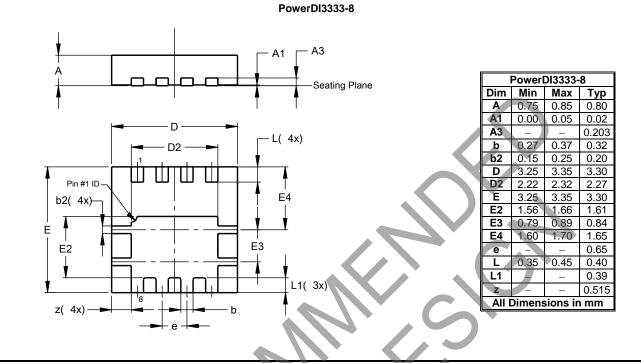
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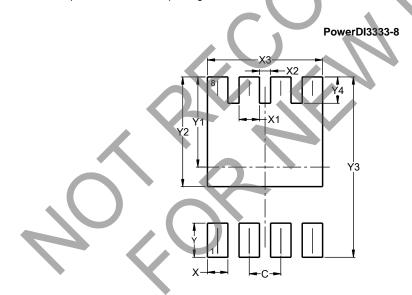
### Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.



## Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.



Dimensions	Value (in mm)
С	0.650
Х	0.420
X1	0.420
X2	0.230
X3	2.370
Y	0.700
Y1	1.850
Y2	2.250
Y3	3.700
Y4	0.540



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